



# N-Channel NexFET™ Power MOSFET

Check for Samples: CSD16404Q5A

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas

#### **FEATURES**

- Ultralow Q<sub>q</sub> and Q<sub>qd</sub>
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- Halogen Free
- SON 5-mm × 6-mm Plastic Package

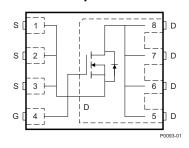
### **APPLICATIONS**

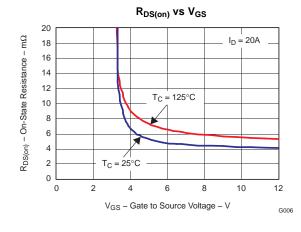
- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and Computing Systems
- Optimized for Control FET Applications

#### **DESCRIPTION**

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.







#### PRODUCT SUMMARY

V <sub>DS</sub>	Drain to Source Voltage	25	V	
$Q_g$	Gate Charge Total (4.5V)	6.5	nC	
$Q_{gd}$	Gate Charge Gate to Drain	1.7		nC
D	Drain to Source On Resistance	V <sub>GS</sub> = 4.5V	5.7	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	V <sub>GS</sub> = 10V	4.1	mΩ
V <sub>GS(th)</sub>	Threshold Voltage	1.8	V	

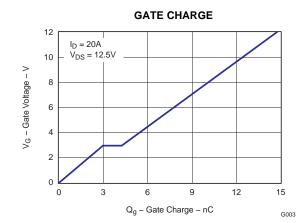
#### **ORDERING INFORMATION**

Device	Package	Media	Qty	Ship
CSD16404Q5A	SON 5-mm × 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel

#### **ABSOLUTE MAXIMUM RATINGS**

T <sub>A</sub> = 2	5°C unless otherwise stated	VALUE	UNIT					
$V_{DS}$	Drain to Source Voltage	25	٧					
$V_{GS}$	Gate to Source Voltage	+16 / -12	V					
	Continuous Drain Current, T <sub>C</sub> = 25°C	81	Α					
I <sub>D</sub>	Continuous Drain Current <sup>(1)</sup>	21	Α					
$I_{DM}$	Pulsed Drain Current, T <sub>A</sub> = 25°C <sup>(2)</sup>	135	Α					
$P_D$	Power Dissipation <sup>(1)</sup>	3	W					
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to 150	°C					
E <sub>AS</sub>	Avalanche Energy, single pulse $I_D = 40A$ , $L = 0.1mH$ , $R_G = 25\Omega$	80	mJ					

- (1)  $R_{\theta JA} = 41^{\circ} C/W$  on 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4 PCB.
- (2) Pulse duration ≤300µs, duty cycle ≤2%



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## **ELECTRICAL CHARACTERISTICS**

T<sub>A</sub> = 25°C, unless otherwise specified

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static C	haracteristics		·			
BV <sub>DSS</sub>	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	25			V
I <sub>DSS</sub>	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = 20V$			1	μΑ
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = +16/-12V$			100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.4	1.8	2.1	V
D	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 20A$		5.7	7.2	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = 10V, I_D = 20A$		4.1	5.1	mΩ
g <sub>fs</sub>	Transconductance	$V_{DS} = 15V, I_D = 20A$		57		S
Dynamic	Characteristics	·	•		·	
C <sub>ISS</sub>	Input Capacitance			940	1220	pF
Coss	Output Capacitance	$V_{GS} = 0V$ , $V_{DS} = 12.5V$ , $f = 1MHz$		810	1050	pF
$C_{RSS}$	Reverse Transfer Capacitance			62	80	pF
$R_g$	Series Gate Resistance			0.9	1.8	Ω
$Q_g$	Gate Charge Total (4.5V)			6.5	8.5	nC
$Q_{gd}$	Gate Charge Gate to Drain	V 42.5V L 20A		1.7		nC
Q <sub>gs</sub>	Gate Charge Gate to Source	$V_{DS} = 12.5V, I_D = 20A$		3		nC
$Q_{g(th)}$	Gate Charge at Vth			1.5		nC
Q <sub>OSS</sub>	Output Charge	$V_{DS} = 13V, V_{GS} = 0V$		16		nC
t <sub>d(on)</sub>	Turn On Delay Time			7.8		ns
t <sub>r</sub>	Rise Time	$V_{DS} = 12.5V, V_{GS} = 4.5V,$		13.4		ns
t <sub>d(off)</sub>	Turn Off Delay Time	$I_D = 20A$ , $R_G = 2\Omega$		8.4		ns
t <sub>f</sub>	Fall Time			4.6		ns
Diode C	haracteristics					
V <sub>SD</sub>	Diode Forward Voltage	$I_{S} = 20A, V_{GS} = 0V$		0.85	1	V
Q <sub>rr</sub>	Reverse Recovery Charge	$V_{DD} = 13V$ , $I_F = 20A$ , $di/dt = 300A/\mu s$		20		nC
t <sub>rr</sub>	Reverse Recovery Time	$V_{DD} = 13V$ , $I_F = 20A$ , $di/dt = 300A/\mu s$		22		ns

#### THERMAL CHARACTERISTICS

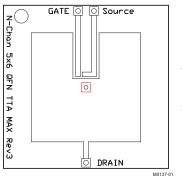
T<sub>A</sub> = 25°C, unless otherwise specified

	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case <sup>(1)</sup>			3.3	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient (1) (2)			52	°C/W

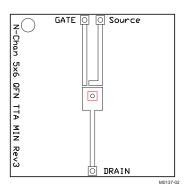
 $R_{\theta JC}$  is determined with the device mounted on a 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB.  $R_{\theta JC}$  is specified by design, whereas  $R_{\theta JA}$  is determined by the user's board design. Device mounted on FR4 material with 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu.

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Max  $R_{\theta JA} = 52^{\circ} C/W$  when mounted on 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max  $R_{\theta JA} = 120^{\circ} C/W$  when mounted on minimum pad area of 2-oz. (0.071-mm thick) Cu.

#### TYPICAL MOSFET CHARACTERISTICS

T<sub>A</sub> = 25°C, unless otherwise specified

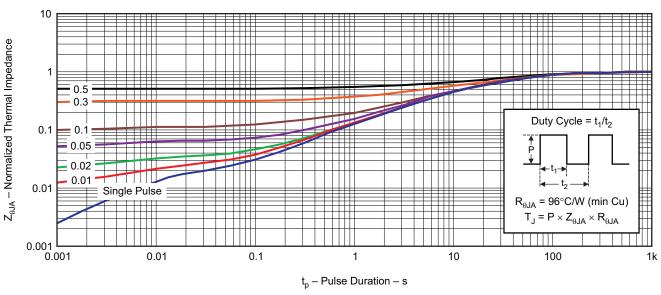


Figure 1. Transient Thermal Impedance

G012



## TYPICAL MOSFET CHARACTERISTICS (continued)

## T<sub>A</sub> = 25°C, unless otherwise specified

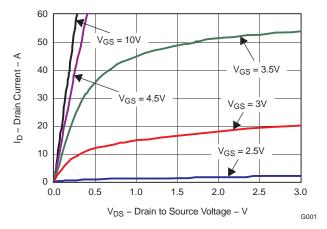


Figure 2. Saturation Characteristics

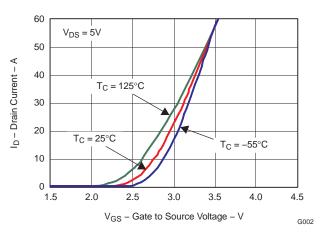


Figure 3. Transfer Characteristics

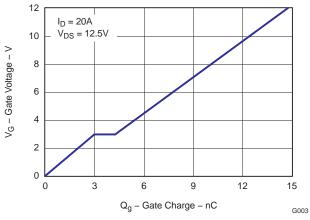


Figure 4. Gate Charge

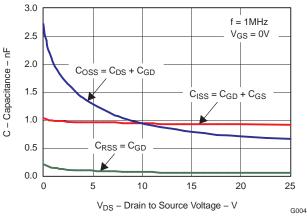


Figure 5. Capacitance

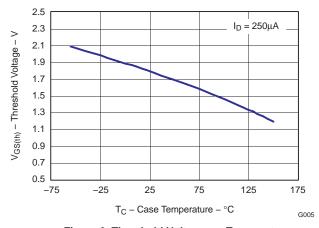


Figure 6. Threshold Voltage vs. Temperature

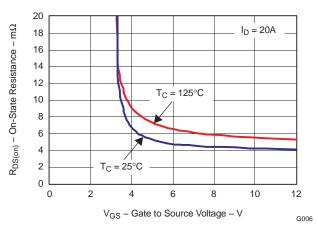


Figure 7. On-State Resistance vs. Gate to Source Voltage



## TYPICAL MOSFET CHARACTERISTICS (continued)

## $T_A = 25$ °C, unless otherwise specified

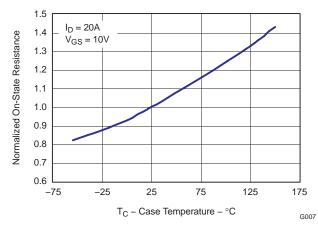


Figure 8. Normalized On-State Resistance vs. Temperature

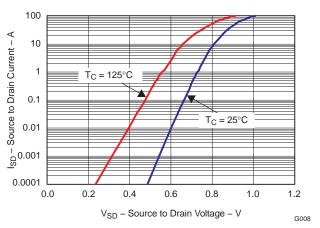


Figure 9. Typical Diode Forward Voltage

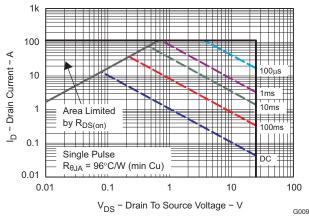


Figure 10. Maximum Safe Operating Area

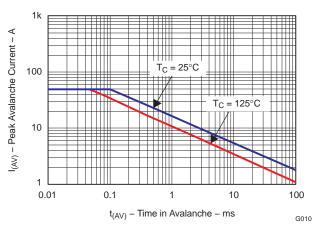


Figure 11. Single Pulse Unclamped Inductive Switching

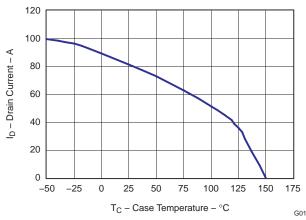
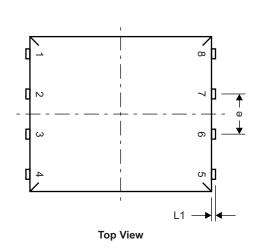


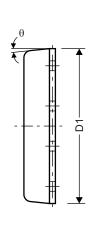
Figure 12. Maximum Drain Current vs. Temperature



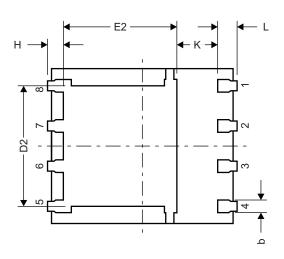
## **MECHANICAL DATA**

# **Q5A Package Dimensions**

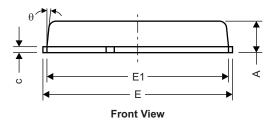




Side View



**Bottom View** 



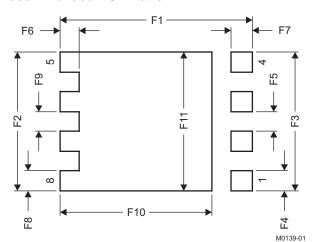
M0135-01

DIM	MILLIMETERS						
DIM	MIN	NOM	MAX				
А	0.90	1.00	1.10				
b	0.33	0.41	0.51				
С	0.20	0.25	0.30				
D1	4.80	4.90	5.00				
D2	3.61	3.81	3.96				
E	5.90	6.00	6.10				
E1	5.70	5.75	5.80				
E2	3.38	3.58	3.78				
е		1.27 BSC					
Н	0.41	0.51	0.61				
К	1.10						
L	0.51	0.61	0.71				
L1	0.06	0.13	0.20				
θ	0°		12°				

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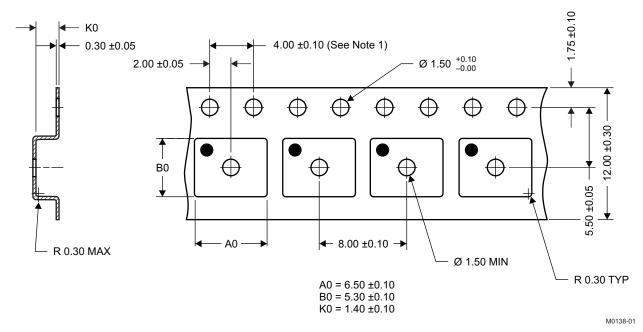
#### **Recommended PCB Pattern**



DIM	MILLIN	METERS	INCHES		
DIN	MIN	MAX	MIN	MAX	
F1	6.205	6.305	0.244	0.248	
F2	4.46	4.56	0.176	0.18	
F3	4.46	4.56	0.176	0.18	
F4	0.65	0.7	0.026	0.028	
F5	0.62	0.67	0.024	0.026	
F6	0.63	0.68	0.025	0.027	
F7	0.7	0.8	0.028	0.031	
F8	0.65	0.7	0.026	0.028	
F9	0.62	0.67	0.024	0.026	
F10	4.9	5	0.193	0.197	
F11	4.46	4.56	0.176	0.18	

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

## **Q5A Tape and Reel Information**



Notes: 1. 10-sprocket hole-pitch cumulative tolerance ±0.22

- 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm, unless otherwise specified.
- 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket
- 6. MSL1 260°C (IR and convection) PbF reflow compatible

## SLPS198B - AUGUST 2009-REVISED APRIL 2010



## **REVISION HISTORY**

Changes from Original (August 2009) to Revision A		
Changed Figure 10 - Maximum Safe Operating Area, Drain Current top scale From: 100ms T	o: 100µs 5	
Changes from Revision A (September 2009) to Revision B	Page	
Deleted the Package Marking Information section	7	

## PACKAGE MATERIALS INFORMATION

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## TAPE AND REEL INFORMATION





_		
		Dimension designed to accommodate the component width
	B0	Dimension designed to accommodate the component length
	K0	Dimension designed to accommodate the component thickness
	W	Overall width of the carrier tape
ı	P1	Pitch between successive cavity centers

## QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD16404Q5A	VSONP	DQJ	8	2500	330.0	12.4	6.3	5.3	1.2	8.0	12.0	Q1

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#### \*All dimensions are nominal

Device	Device Package Type		Package Drawing Pins		Length (mm)	Width (mm)	Height (mm)	
CSD16404Q5A	VSONP	DQJ	8	2500	340.0	340.0	38.0	

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